



DMP2047UCB4

#### Product Summary (Typ. @ V<sub>GS</sub> = -4.5V, T<sub>A</sub> = +25°C)

BVDSS	RDS(ON)	Qg	Qgd	ID
-20V	40mΩ	2.3nC	0.4nC	-4.1A

#### Description

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

- Battery Management
- Load Switch
- Battery Protection

## Features

• LD-MOS Technology with the Lowest Figure of Merit:  $R_{DS(ON)} = 40m\Omega$  to Minimize On-State Losses  $Q_g = 2.3nC$  for Ultra-Fast Switching

P-CHANNEL ENHANCEMENT MODE MOSFET

- V<sub>GS(th)</sub> = -0.8V typ. for a Low Turn-On Potential
- CSP with Footprint 1.0mm × 1.0mm
- Height = 0.62mm for Low Profile
- ESD = 3kV HBM Protection of Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at

https://www.diodes.com/products/automotive/automotiveproducts/.

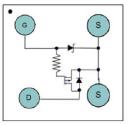
 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <u>https://www.diodes.com/quality/product-definitions/</u>

### **Mechanical Data**

- Case: U-WLB1010-4
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminal: Finish SnAgCu. Solderable per MIL-STD-202 Method
  208
- Weight: 0.0018 grams (Approximate)

#### U-WLB1010-4





Top View Equivalent Circuit

#### Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2047UCB4-7	U-WLB1010-4	3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



## **Marking Information**

#### U-WLB1010-4



DW = Product Type Marking Code  $\begin{array}{l} YM = \text{Date Code Marking } \\ YM = \text{Date Code Marking} \\ Y = \text{Year (ex: H = 2020)} \\ M = \text{Month (ex: 9 = \text{September)}} \end{array}$ c = Assembly Code

Date Code Key

Year	2012		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	Z		Н		J	К	L	М	Ν	0	Р	R
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec

#### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	VDSS	-20	V		
Gate-Source Voltage			V <sub>GSS</sub>	-6	V
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	D	-4.1 -3.2	А
Continuous Drain Current (Note 5) $V_{GS}$ = -2.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ID	-3.6 -2.8	A
Pulsed Drain Current (Note 6)	Ідм	-16	А		

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	PD	1.0	W
Thermal Resistance, Junction to Ambient @ $T_A = +25$ °C (Note 7)	R <sub>0JA</sub>	127	°C/W
Thermal Resistance, Junction to Case @ $T_C = +25^{\circ}C$ (Note 7)	Rejc	25.8	°C/W
Power Dissipation (Note 5)	PD	1.66	W
Thermal Resistance, Junction to Ambient @ $T_A = +25^{\circ}C$ (Note 5)	R <sub>0JA</sub>	77	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Notes: 5. Device mounted on FR4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.

Repetitive rating, pulse width limited by junction temperature.
 Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.



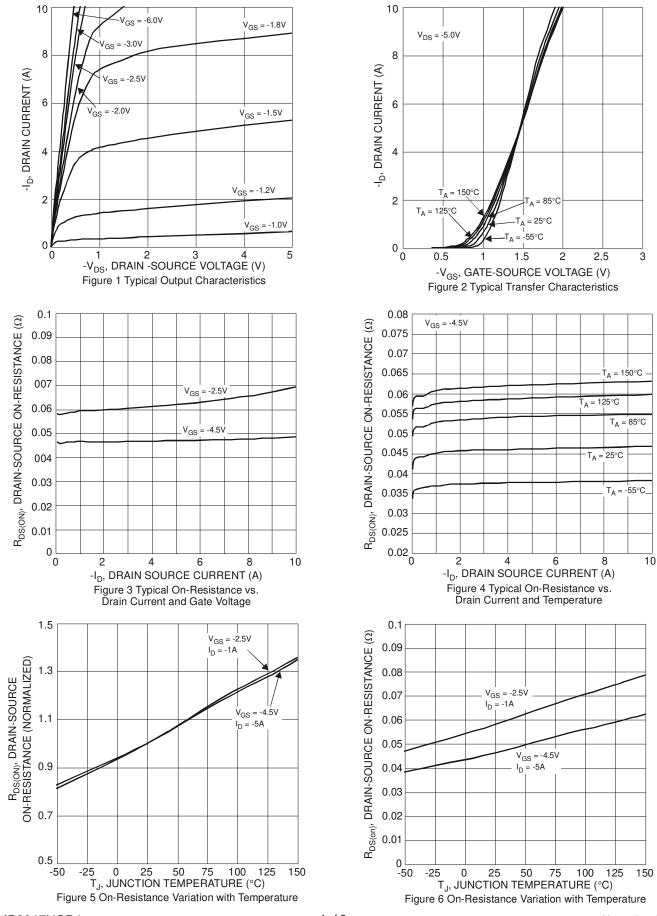
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Cumphed	Min	T.m	Max	Unit	Test Condition
	Symbol	WIIN	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)			1	1		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	—	V	$V_{GS} = 0V, I_D = -250 \mu A$
Gate-Source Breakdown Voltage	BVGSS	-6.0		—	V	$V_{DS} = 0V, I_{G} = -250\mu A$
Zero Gate Voltage Drain Current TJ = +25°C	IDSS	_	—	-1	μA	$V_{DS} = -16V, V_{GS} = 0V$
Gate-Source Leakage	IGSS	—		-100	nA	$V_{GS}=-6V,V_{DS}=0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	VGS(TH)	-0.4	-0.8	-1.2	V	$V_{DS} = V_{GS}$ , $I_D = -250 \mu A$
Static Drain-Source On-Resistance	Descer	—	40	47	mΩ	VGS = -4.5V, ID =-1A
	RDS(ON)		53	60	11122	$V_{GS} = -2.5V, I_D = -1A$
Forward Transfer Admittance	Y <sub>fs</sub>	_	3.7	—	S	VDS = -10V, ID = -1A
Diode Forward Voltage	Vsd		-0.7	-1.0	V	Vgs = 0V, Is = -1A
Reverse Recovery Charge	QRR	_	3.07	_	nC	V <sub>DD</sub> = -10V, I <sub>F</sub> = -1A,
Reverse Recovery Time	trr	_	13.14	_	ns	di/dt =100A/µs
DYNAMIC CHARACTERISTICS (Note 9)						·
Input Capacitance	Ciss		218	_		$V_{DS} = -10V, V_{GS} = 0V,$ f = 1.0MHz
Output Capacitance	Coss		116	_	pF	
Reverse Transfer Capacitance	Crss		11	_		1 = 1.0MHz
Total Gate Charge	Qg	_	2.3	_		
Gate-Source Charge	Qgs	_	0.2	—	nC	VGS = -4.5V, VDS = -10V,
Gate-Drain Charge	Q <sub>gd</sub>	_	0.4	—	nC	I <sub>D</sub> = -1A
Gate Charge at Vth	Qg(th)	_	0.2	—		
Turn-On Delay Time	tD(ON)	_	7.9	—		
Turn-On Rise Time	t <sub>R</sub>	_	10.7	—	1	$V_{DS} = -10V, V_{GS} = -2.5V,$
Turn-Off Delay Time	tD(OFF)	_	48	_	ns	$R_G = 20\Omega, I_D = -1A$
Turn-Off Fall Time	tF		38	_		

8. Short duration pulse test used to minimize self-heating effect.9. Guaranteed by design. Not subject to production testing. Notes:



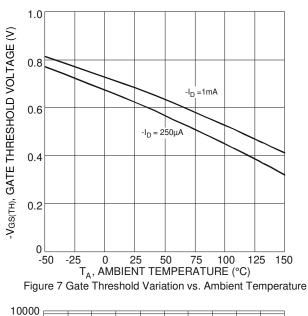
## DMP2047UCB4

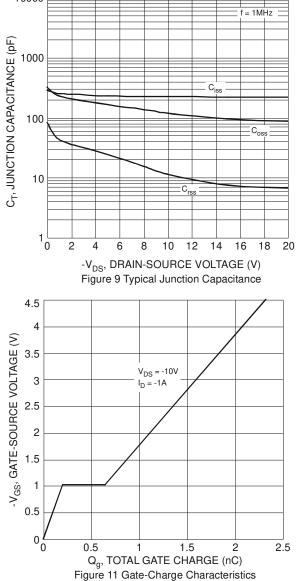


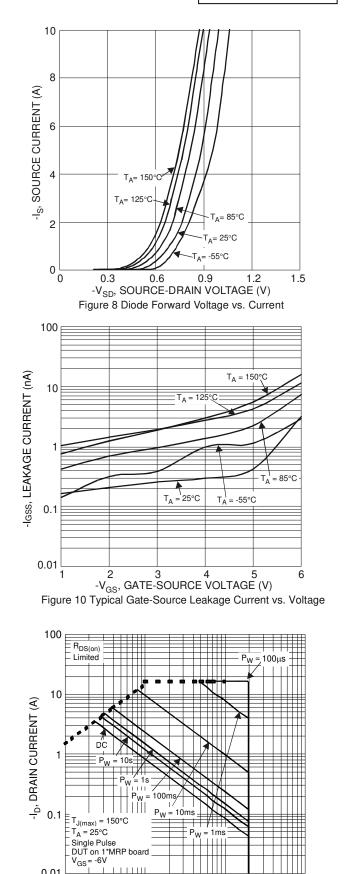
DMP2047UCB4 Document number: DS36154 Rev. 7 - 2 November 2020 © Diodes Incorporated



## DMP2047UCB4







0.01 0.1

100

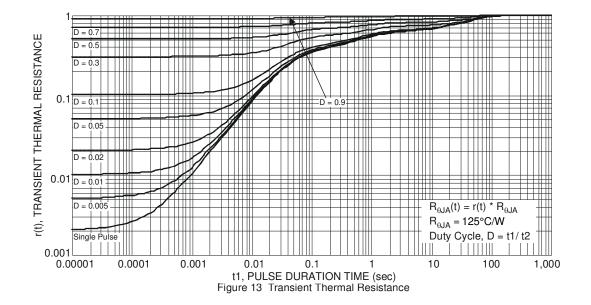
1m

10

-V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)

Figure 12 SOA, Safe Operation Area

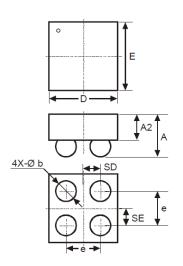






# Package Outline Dimensions

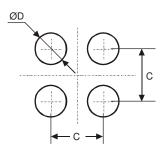
Please see http://www.diodes.com/package-outlines.html for the latest version.



U-WLB1010-4							
Dim	Min	Max	Тур				
D	0.95	1.05	1.00				
ш	0.95	1.05	1.00				
Α	-	0.62	-				
A2	-	-	0.38				
b	0.25	0.35	0.30				
e	-	-	0.50				
SD	-	-	0.25				
SE	-	-	0.25				
All	Dimens	ions in I	nm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



#### U-WLB1010-4

Dimensions	Value (in mm)
С	0.50
D	0.25

U-WLB1010-4



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